

L Number	Hits	Search Text	DB	Time stamp
1	376	438/259.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:27
2	1656	438/270.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 08:31
3	111	438/270.ccls. and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:24
4	22	438/271.ccls. and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:27
5	13	438/272.ccls. and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:39
6	35	(extended adj trench) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:32
7	121	extended adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:37
8	18	segmented adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:38
9	3	438/242.ccls. and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:40
10	137	438/242.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:49
11	0	gate adj botton adj second adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:49
12	0	gate adj formed adj botton adj second adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:49
13	0	gate adj formed adj botton adj extended adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:50
14	0	gate adj formed adj botton adj deep adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:50

15	1	gate adj formed adj deep adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:50
16	223	gate adj formed adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:51
17	32	(gate adj formed adj trench) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:53
18	0	source adj region adj spaced adj apart adj first adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 09:54
19	3	source adj region adj spaced adj apart adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 10:23
20	0	20020113263.pn. and (gate with doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 10:23
21	0	20020113263.pn. and (gate same doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 10:23
22	2	20020113263.pn. and (gate same conductivity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 10:59
23	1	6673681.pn. and (gate with doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 10:25
24	2	6673681.pn. and (gate same doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 12:05
25	1	20020113263.pn. and vertical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:10
26	0	(vertical adj (fet or (field adj effect adj transistor))) and ((gaas or (gallium adj arsenide)) adj body)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:12
27	155	(vertical adj (fet or (field adj effect adj transistor))) and (gaas or (gallium adj arsenide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:23
28	499	(semiconductor adj body) with ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:26

29	21	((semiconductor adj body) with ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)))) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:25
30	499	(semiconductor adj body) with ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:26
31	36	438/259.ccls. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:31
32	118	438/270.ccls. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:34
33	19	438/271.ccls. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:35
34	8	438/272.ccls. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:39
35	24	passivation adj stack	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:41
36	44	plurality adj passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:43
37	57	(double or dual) adj passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:46
38	43	(trench) adj passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:48
39	74	(trench) near passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 11:48
40	2	6277751.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 12:48
41	0	4816884.pn. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 12:49
42	0	4824793.pn. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 12:50

43	0	4833516.pn. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 12:50
44	0	4661832.pn. and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 12:50
46	511	drift and trench and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 12:56
47	22	drift and trench and ((gaas or (gallium adj arsenide)) or (inp or (indium adj phosphide)) or iiiv) and (depletion adj mode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 13:26
48	3	drift and trench and (n adj channel adj depletion adj mode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/06 13:27
-	64	double adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:36
-	1420	(trench adj trench) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 15:46
-	16	(trench adj "within" adj trench) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 15:48
-	0	(trench adj "within" adj trench) and (drift adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 15:49
-	47	(trench adj trench) and (drift adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 15:52
-	0	(dual adj trench) and (drift adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 15:53
-	354	(trench) and (drift adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:05
-	578	(gate adj trench) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:08
-	0	(double adj recess adj substrate) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:09

-	0	double adj recess adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:09
-	0	double adj recessed adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:09
-	0	dual adj recessed adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:09
-	0	multiple adj recessed adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:10
-	5	multiple adj groove adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:10
-	0	double adj groove adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:11
-	0	double adj mesa adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:11
-	104	double adj damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:14
-	126	(first adj trench) and (second adj trench) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:24
-	8	(upper adj trench) and (lower adj trench) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:25
-	1	(trench adj first adj width) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:26
-	0	(trench adj first adj length) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:26
-	2	trench adj first adj length	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:27
-	51	trench adj first adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:33

-	0	trench adj "having" adj first adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:33
-	346	recessed adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:35
-	193	(recessed adj trench) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:44
-	33	(vertical adj fet) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:46
-	169	(vertical adj fet) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:56
-	28	(vertical adj fet) and (deep adj trench) and (shallow adj trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:57
-	963	(deep adj trench) and (shallow adj trench) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:58
-	371	((deep adj trench) with (shallow adj trench)) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 17:04
-	56	((deep adj trench) near (shallow adj trench)) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 16:59
-	18	((deep adj trench) with (shallow adj trench)) and 257/\$.ccls. and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:18
-	140	(gate adj trench) and 257/\$.ccls. and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:30
-	0	(first adj trench adj "within" adj second adj trench) and 257/\$.ccls. and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:31
-	0	first adj trench adj "within" adj second adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:31
-	0	first adj trench adj second adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/05 18:31

-	368	(first adj trench) near (second adj trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/05 18:32
-	40	((first adj trench) near (second adj trench)) and drift	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/05 18:35
-	0	double adj etched adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/05 18:36
-	141	double near trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/05 18:41
-	16	interconnected adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/05 18:54
-	499	257/302.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/05 18:55